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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MMBT123S

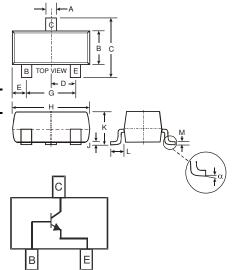
1A NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23							
Dim	Min	Max					
Α	0.37	0.51					
В	1.20	1.40					
С	2.30	2.50					
D	0.89	1.03					
Е	0.45	0.60					
G	1.78	2.05					
Н	2.80	3.00					
J	0.013	0.10					
K	0.903	1.10					
L	0.45	0.61					
М	0.085	0.180					
α	0°	8°					
All Dimensions in mm							

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V_{CBO}	45	V	
Collector-Emitter Voltage	V _{CEO}	18	V	
Emitter-Base Voltage	V _{EBO}	5	V	
Collector Current - Continuous	I _C	1	Α	
Power Dissipation (Note 1)	P _D	300	mW	
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

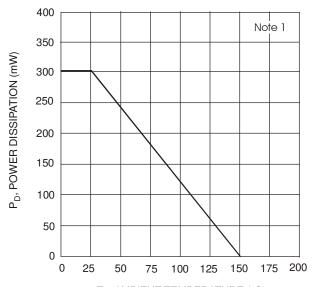
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 3)								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	45	_	V	$I_C = 100 \mu A, I_E = 0$			
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	18	_	V	$I_C = 1 \text{ mA}, I_B = 0$			
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	_	V	$I_E = 100 \mu A, I_C = 0$			
Collector Cutoff Current	I _{CBO}	_	1	μΑ	$V_{CB} = 40V, I_{E} = 0$			
Emitter Cutoff Current	I _{EBO}	_	1	μΑ	$V_{EB} = 4V$, $I_C = 0$			
ON CHARACTERISTICS (Note 3)	•		,					
DC Current Gain	h _{FE}	150	800		$I_C = 100 \text{mA}, V_{CE} = 1 \text{V}$			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.5	V	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$			
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	C _{obo}	_	8	рF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$			
Current Gain-Bandwidth Product	f _T	100	_	MHz	$V_{CB} = 10V, I_E = 50mA,$ f = 100MHz			

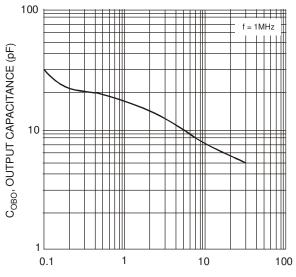
Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead. Halogen and Antimony Free.
- Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

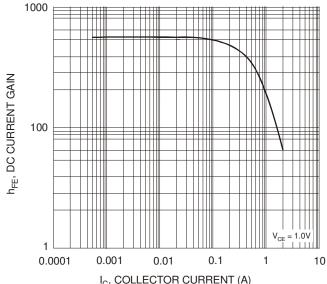




T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



 V_{CB} , COLLECTOR-BASE VOLTAGE (V) Fig. 3, Output Capacitance vs. Collector-Base Voltage



I_C, COLLECTOR CURRENT (A) Fig. 2, Typical DC Current Gain vs Collector Current

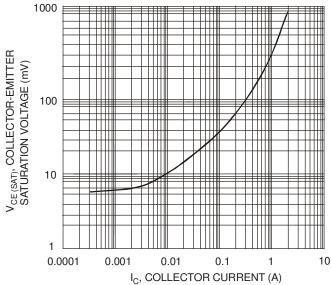


Fig. 4, Collector Saturation Voltage vs Collector Current

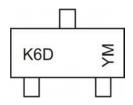


Ordering Information (Note 5)

Device	Packaging	Shipping			
MMBT123S-7-F	SOT-23	3000/Tape & Reel			

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K6D = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	200	6 20	07 2	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т	l	J	V	W	Χ	Υ	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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